



April 2000

QFET™

FQPF17N40

400V N-Channel MOSFET

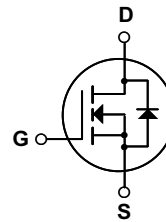
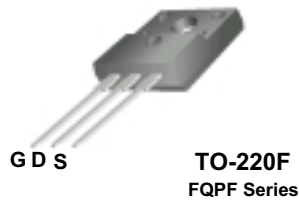
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, electronic lamp ballast based on half bridge.

Features

- 9.5A, 400V, $R_{DS(on)} = 0.27\Omega @ V_{GS} = 10V$
- Low gate charge (typical 45 nC)
- Low Crss (typical 30 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQPF17N40	Units
V _{DSS}	Drain-Source Voltage	400	V
I _D	Drain Current - Continuous (T _C = 25°C)	9.5	A
	- Continuous (T _C = 100°C)	6.0	A
I _{DM}	Drain Current - Pulsed (Note 1)	38	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	1000	mJ
I _{AR}	Avalanche Current (Note 1)	9.5	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	5.6	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P _D	Power Dissipation (T _C = 25°C)	56	W
	- Derate above 25°C	0.45	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	2.23	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	400	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.44	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 400 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 320 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA

On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.75 A	--	0.21	0.27	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 4.75 A (Note 4)	--	10	--	S

Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1800	2300	pF
C _{oss}	Output Capacitance		--	270	350	pF
C _{rss}	Reverse Transfer Capacitance		--	30	40	pF

Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 200 V, I _D = 17.2 A, R _G = 25 Ω (Note 4, 5)	--	40	90	ns
t _r	Turn-On Rise Time		--	185	380	ns
t _{d(off)}	Turn-Off Delay Time		--	90	190	ns
t _f	Turn-Off Fall Time		--	105	220	ns
Q _g	Total Gate Charge	V _{DS} = 320 V, I _D = 17.2 A, V _{GS} = 10 V (Note 4, 5)	--	45	60	nC
Q _{gs}	Gate-Source Charge		--	11.4	--	nC
Q _{gd}	Gate-Drain Charge		--	21.7	--	nC

Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current	--	--	9.5	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	38	A	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 9.5 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 17.2 A, di _F / dt = 100 A/μs (Note 4)	--	290	--	ns
Q _{rr}	Reverse Recovery Charge		--	2.5	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 19.4mH, I_{AS} = 9.5A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 17.2A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

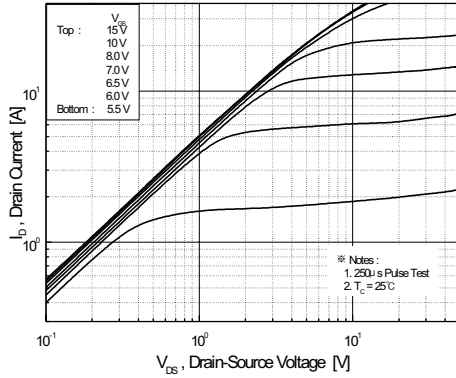


Figure 1. On-Region Characteristics

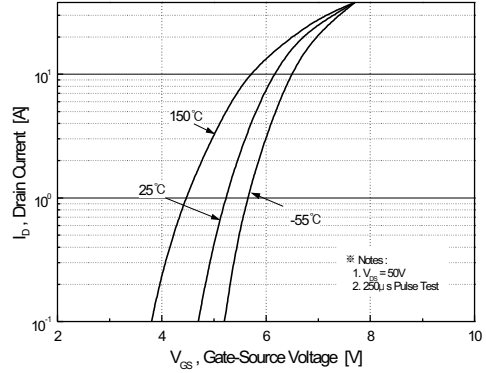


Figure 2. Transfer Characteristics

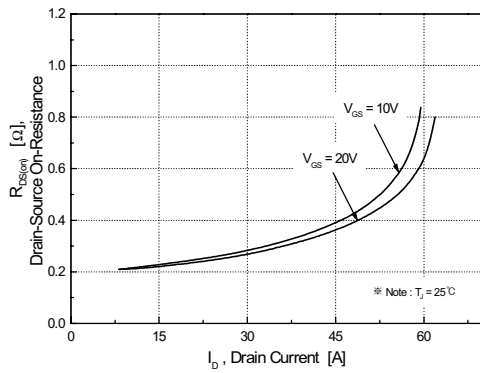


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

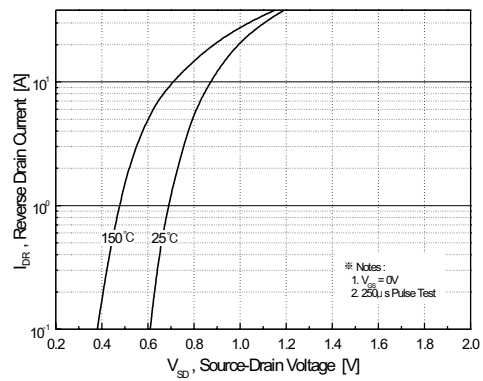


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

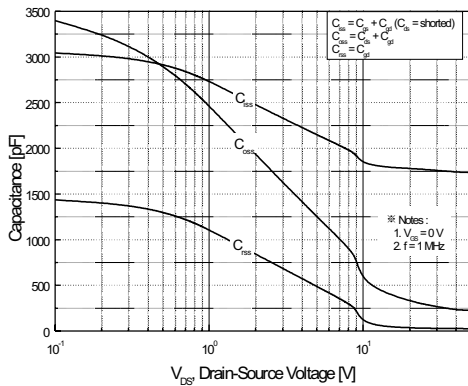


Figure 5. Capacitance Characteristics

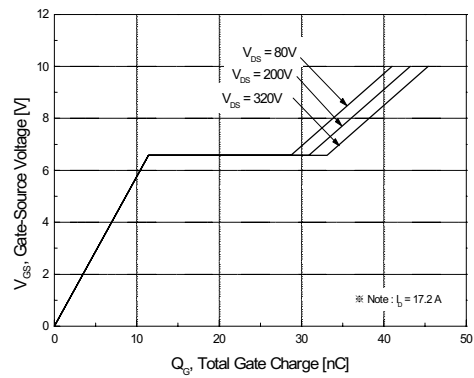


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

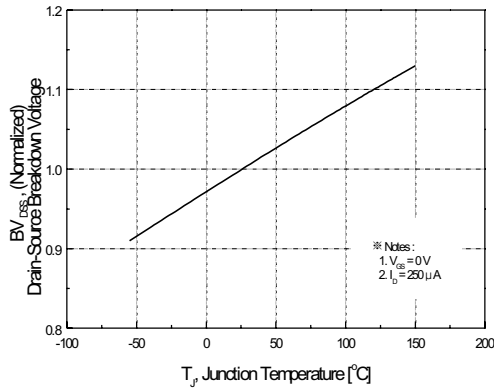


Figure 7. Breakdown Voltage Variation vs. Temperature

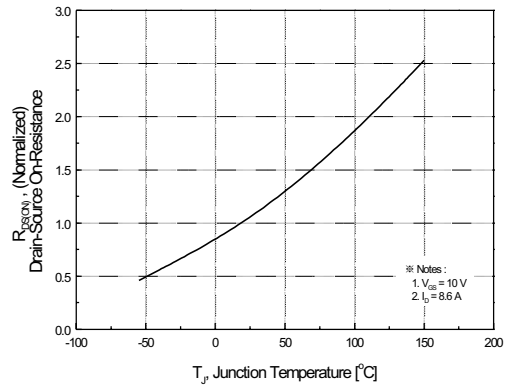


Figure 8. On-Resistance Variation vs. Temperature

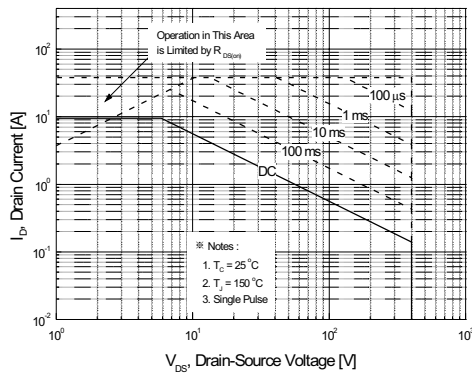


Figure 9. Maximum Safe Operating Area.

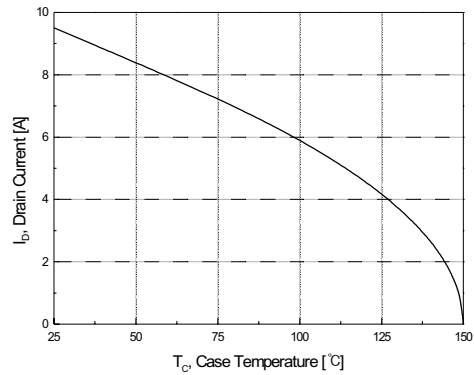


Figure 10. Maximum Drain Current vs Case Temperature.

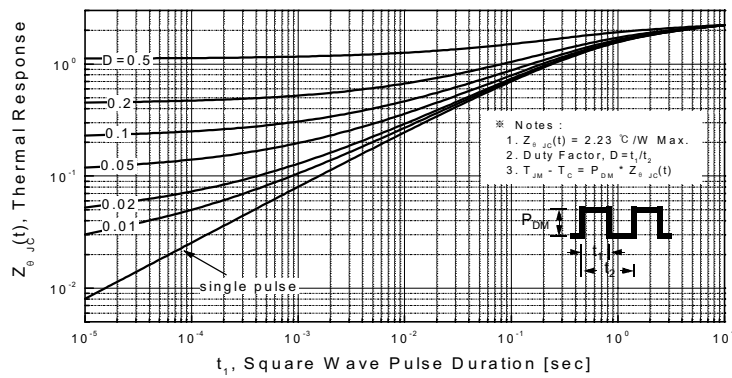


Figure 11. Transient Thermal Response Curve

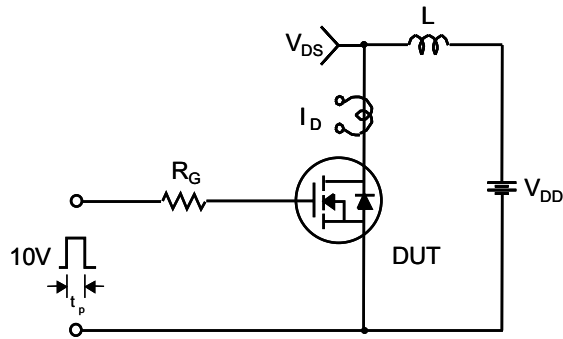
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220F



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FAST®	Quiet Series™	
FAST _r ™	SuperSOT™-3	
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